Amendments To Claims

Listing Of Claims

Claims 1-128 (canceled)

129. (previously presented) A method for fabricating semiconductor components comprising:

providing a plurality of semiconductor dice on a substrate having a first side, a second side, and a plurality of die contacts on the first side;

forming a first polymer dam on the first side of the substrate configured to encircle at least some of the dice;

forming a plurality of contact bumps on the die contacts;

forming a polymer layer on the first side within the first polymer dam;

forming a second polymer dam on the first side configured to support peripheral areas of the substrate;

thinning the substrate from the second side;

forming a plurality of terminal contacts on the contact bumps; and

singulating the dice from the substrate.

- 130. (previously presented) The method of claim 129 further comprising following the thinning step applying a polymer tape to the second side.
- 131. (previously presented) The method of claim 130 wherein the polymer tape comprises a wafer level underfill material.
- 132. (previously presented) The method of claim 130 further comprising laser marking the polymer tape.

- 133. (previously presented) The method of claim 130 wherein the polymer tape is opaque to a radiation used for marking the polymer tape.
- 134. (previously presented) The method of claim 129 further comprising following the thinning step, attaching a heat sink to the second side.
- 135. (previously presented) The method of claim 129 wherein the first polymer dam encircles only the complete dice on the substrate.
- 136. (previously presented) The method of claim 129 further comprising testing the dice on the substrate prior to the singulating step.
- 137. (previously presented) A method for fabricating semiconductor components comprising:

providing a plurality of semiconductor dice on a substrate having a first side, a second side, and a plurality of die contacts on the first side;

forming a first polymer dam on the first side of the substrate configured to encircle at least some of the dice;

forming a second polymer dam on the first side configured to support peripheral areas of the substrate;

forming a polymer layer on the first side within the first polymer dam;

thinning the substrate from the second side;

singulating the dice from the substrate to form each component with a first side encapsulated by the polymer layer and a thinned second side; and

attaching a heat sink to the thinned second side.

138. (previously presented) The method of claim 137 further comprising forming a plurality of terminal contacts

on the polymer layer in electrical communication with the die contacts.

- 139. (previously presented) The method of claim 137 further comprising forming a plurality of contact bumps on the die contacts encapsulated by the polymer layer.
- 140. (previously presented) The method of claim 137 wherein the singulating step is performed by sawing, laser cutting or liquid jet cutting the substrate.
- 141. (previously presented) The method of claim 137 wherein the attaching the heat sink step is performed using a thermally conductive adhesive.
- 142. (previously presented) A method for fabricating semiconductor components comprising:

providing a plurality of semiconductor dice on a substrate having a first side and a second side;

forming a plurality of trenches on the first side in a criss cross pattern between the dice;

forming a plurality of dams in the trenches comprising a first polymer material;

forming a plurality of polymer layers on the first side within the dams comprising a second polymer material;

thinning the substrate from the second side to expose the trenches; and

forming a plurality of grooves through the dams to singulate the dice.

143. (previously presented) The method of claim 142 wherein the first polymer material comprises a photoimageable material.

- 144. (previously presented) The method of claim 142 wherein the first polymer material comprises a 3-D imageable material.
- 145. (previously presented) The method of claim 142 wherein the second polymer material comprises a silicone, a polyimide or an epoxy.
- 146. (previously presented) The method of claim 142 further comprising forming contact bumps on the dice within the polymer layers and forming terminal contacts on the contact bumps.
- 147. (previously presented) A method for fabricating semiconductor components comprising:

providing a semiconductor substrate comprising a plurality of semiconductor dice and having a first side, a second side and a thickness;

forming a plurality of trenches on the first side in a criss-cross pattern along peripheral edges of the dice, each trench having a depth less than the thickness;

depositing an imageable polymer material on the first side and in the trenches;

exposing and developing the imageable polymer material to form polymer dams in the trenches surrounding the dice;

depositing a second polymer material on the dice within the polymer dams;

thinning the substrate from the second side to expose the trenches; and

singulating the dice through the polymer dams such that each component includes a semiconductor die having a surface covered by a portion of the second polymer material and edges covered by portions of the first polymer material.

- 148. (previously presented) The method of claim 147 wherein the imageable polymer material comprises a photoimageable resist.
- 149. (previously presented) The method of claim 147 wherein the imageable polymer material comprises a 3-D imageable material.
- 150. (previously presented) The method of claim 147 wherein the second polymer material has selected electrical characteristics.
- 151. (previously presented) The method of claim 147 further comprising providing the dice with a plurality of die contacts, forming contact bumps on the die contacts embedded in the second polymer material, and forming terminal contacts on the contact bumps.

Claims 152-260 (canceled)